

4-Pin Full Pitch Mini-Flat Package Phototransistor Optocouplers

FODM121 Series, FODM124, FODM2701, FODM2705

Description

The FODM121 series, FODM124, and FODM2701 consists of a gallium arsenide infrared emitting diode driving a phototransistor in a compact 4-pin mini-flat package. The lead pitch is 2.54 mm. The FODM2705 consists of two gallium arsenide infrared emitting diodes connected in inverse parallel for AC operation.

Features

- More than 5 mm Creepage/Clearance
- Compact 4-Pin Surface Mount Package (2.4 mm Maximum Standoff Height)
- Current Transfer Ratio in Selected Groups:
 - ◆ DC Input:
 - FODM121: 50–600%
 - FODM121A: 100–300%
 - FODM121B: 50–150%
 - FODM121C: 100–200%
 - FODM124: 100% MIN
 - FODM2701: 50–300%
 - ◆ AC Input:
 - FODM2705: 50–300%
- Safety and Regulatory Approvals:
 - ◆ UL1577, 3,750 VAC_{RMS} for 1 Minute
 - ◆ DIN-EN/IEC60747-5-5, 565 V Peak Working Insulation Voltage
- This Device is Pb-Free and is RoHS Compliant

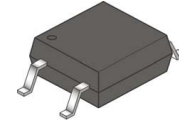
Applications

- Digital Logic Inputs
- Microprocessor Inputs
- Power Supply Monitor
- Twisted Pair Line Receiver
- Telephone Line Receiver



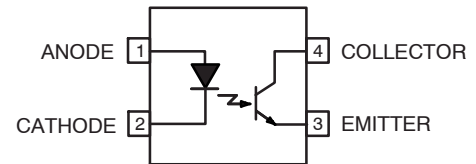
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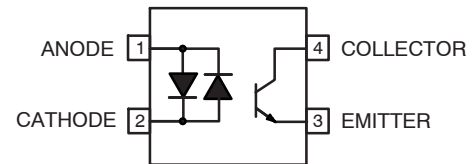


MFP4 3.85X4.4, 2.54P
CASE 100AP

PIN CONNECTIONS

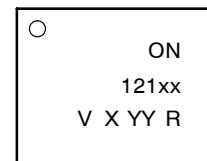


Equivalent Circuit
FODM121, FODM124, FODM2701



Equivalent Circuit
FODM2705

MARKING DIAGRAM



- ON = ON Semiconductor Logo
- 121xx = Device Number
- V = DIN EN/IEC60747-5-5 Option
- X = One-Digit Year Code
- YY = Digit Work Week
- R = Assembly Package Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

FODM121 Series, FODM124, FODM2701, FODM2705

SAFETY AND INSULATION RATINGS

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter	Characteristics	
Installation Classifications per DIN VDE 0110/1.89. For Rated Mains Voltage	< 150 V _{RMS}	I-IV
	< 300 V _{RMS}	I-III
Climatic Classification	40/110/21	
Pollution Degree (DIN VDE 0110/1.89)	2	
Comparative Tracking Index	175	

Symbol	Parameter	Value	Unit
V _{PR}	Input-to-Output Test Voltage, Method A, V _{IORM} × 1.6 = V _{PR} , Type and Sample Test with t _m = 10 s, Partial Discharge < 5 pC	904	V _{peak}
	Input-to-Output Test Voltage, Method B, V _{IORM} × 1.875 = V _{PR} , 100% Production Test with t _m = 1 s, Partial Discharge < 5 pC	1060	V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	565	V _{peak}
V _{IOTM}	Highest Allowable Over-Voltage	6000	V _{peak}
	External Creepage	≥ 5	mm
	External Clearance	≥ 5	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
T _S	Case Temperature (Note 1)	150	°C
I _{S,INPUT}	Input Current (Note 1)	200	mA
P _{S,OUTPUT}	Output Power (Note 1)	300	mW
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500 V (Note 1)	> 10 ⁹	Ω

1. Safety limit values – maximum values allowed in the event of a failure.

ABSOLUTE MAXIMUM RATINGS T_A = 25°C Unless otherwise specified.

Symbol	Parameter	Value	Unit
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TOTAL PACKAGE

T _{STG}	Storage Temperature	-40 to +125	°C
T _{OPR}	Operating Temperature	-40 to +110	°C
T _J	Junction Temperature	-40 to +125	°C
T _{SOL}	Lead Solder Temperature	260 for 10 s	°C

EMITTER

I _{F (avg)}	Continuous Forward Current	50	mA
I _{F (pk)}	Peak Forward Current (1 μs pulse, 300 pps.)	1	A
V _R	Reverse Voltage	6	V
P _D	Power Dissipation	70	mW
	Derate linearly (Above 75°C)	1.41	mW/°C

DETECTOR

I _C	Continuous Collector Current	80	mA	
V _{CEO}	Collector-Emitter Voltage	FODM121 Series, FODM124	80	V
		FODM2701, FODM2705	40	
V _{ECO}	Emitter-Collector Voltage	7	V	
P _D	Power Dissipation	150	mW	
	Derate linearly (Above 80°C)	3.27	mW/°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

FODM121 Series, FODM124, FODM2701, FODM2705

ELECTRICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$ Unless otherwise specified.

Symbol	Parameter	Device	Test Conditions	Min	Typ	Max	Unit
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INDIVIDUAL COMPONENT CHARACTERISTICS

Emitter							
V_F	Forward Voltage	FODM121 Series, FODM124	$I_F = 10\text{ mA}$	1.0	-	1.3	V
		FODM2701	$I_F = 5\text{ mA}$	-	-	1.4	
		FODM2705	$I_F = \pm 5\text{ mA}$	-	-	-	
I_R	Reverse Current	FODM121 Series, FODM124, FODM2701	$V_R = 5\text{ V}$	-	-	5	μA
Detector							
BV_{CEO}	Collector-Emitter Breakdown Voltage	FODM121 Series, FODM124	$I_C = 1\text{ mA}, I_F = 0$	80	-	-	V
		FODM2701, FODM2705		40	-	-	
BV_{ECO}	Emitter-Collector Breakdown Voltage	All	$I_E = 100\text{ }\mu\text{A}, I_F = 0$	7	-	-	V
I_{CEO}	Collector Dark Current	All	$V_{CE} = 40\text{ V}, I_F = 0$	-	-	100	nA
C_{CE}	Capacitance	All	$V_{CE} = 0\text{ V}, f = 1\text{ MHz}$	-	10	-	pF

TRANSFER CHARACTERISTICS

CTR	DC Current Transfer Ratio	FODM2701	$I_F = 5\text{ mA}, V_{CE} = 5\text{ V}$	50	-	300	%
		FODM2705	$I_F = \pm 5\text{ mA}, V_{CE} = 5\text{ V}$	50	-	300	
		FODM121	$I_F = 5\text{ mA}, V_{CE} = 5\text{ V}$	50	-	600	
		FODM121A		100	-	300	
		FODM121B		50	-	150	
		FODM121C		100	-	200	
		FODM124	$I_F = 1\text{ mA}, V_{CE} = 0.5\text{ V}$	100	-	1200	
		FODM124	$I_F = 0.5\text{ mA}, V_{CE} = 1.5\text{ V}$	50	-	-	
	CTR Symmetry	FODM2705	$I_F = \pm 5\text{ mA}, V_{CE} = 5\text{ V}$	0.3	-	3.0	
$V_{CE(SAT)}$	Saturation Voltage	FODM121 Series	$I_F = 8\text{ mA}, I_C = 2.4\text{ mA}$	-	-	0.4	V
		FODM124	$I_F = 1\text{ mA}, I_C = 0.5\text{ mA}$	-	-	0.4	
		FODM2701	$I_F = 10\text{ mA}, I_C = 2\text{ mA}$	-	-	0.3	
		FODM2705	$I_F = \pm 10\text{ mA}, I_C = 2\text{ mA}$	-	-	0.3	
t_r	Rise Time (Non-Saturated)	All	$I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, R_L = 100\text{ }\Omega$	-	3	-	μs
t_f	Fall Time (Non-Saturated)	All	$I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, R_L = 100\text{ }\Omega$	-	3	-	μs

ISOLATION CHARACTERISTICS

V_{ISO}	Steady State Isolation Voltage (Note 2)	All	1 minute	3750	-	-	$V_{AC_{RMS}}$
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Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Steady state isolation voltage, V_{ISO} , is an internal device dielectric breakdown rating. For this test, pins 1 and 2 are common, and pins 3 and 4 are common.

TYPICAL PERFORMANCE CURVES

($T_A = 25^\circ\text{C}$ unless otherwise specified)

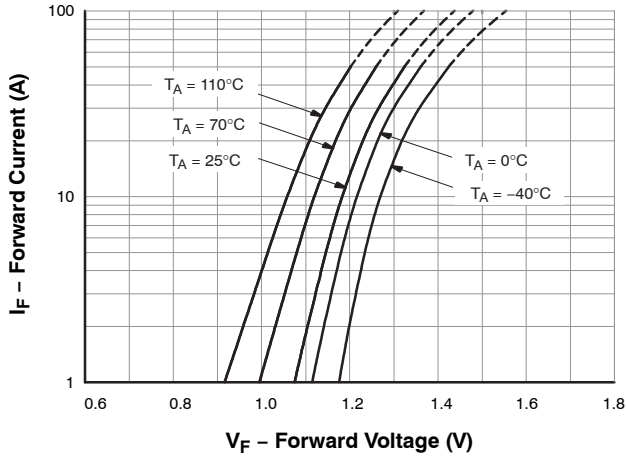


Figure 1. Forward Current vs. Forward Voltage

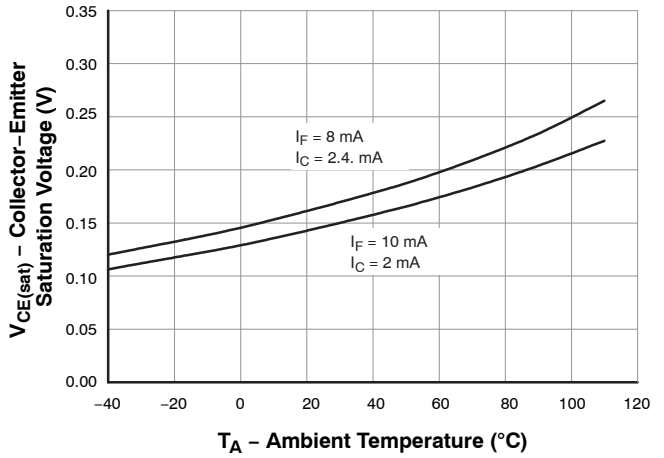


Figure 2. Collector-Emitter Saturation Voltage vs. Ambient Temperature (FODM121/2701/2705)

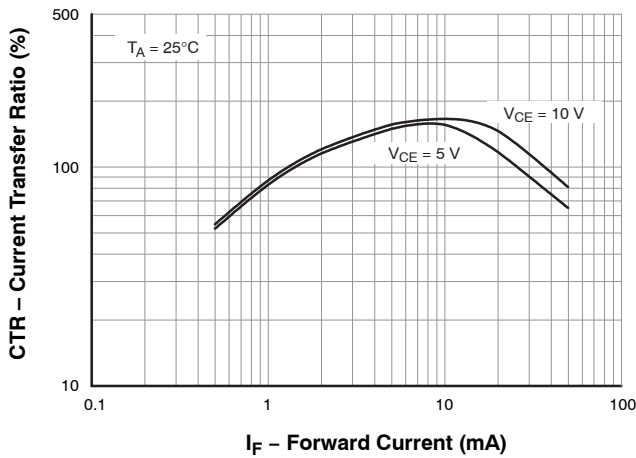


Figure 3. Current Transfer Ratio vs. Forward Current (FODM121/2701/2705)

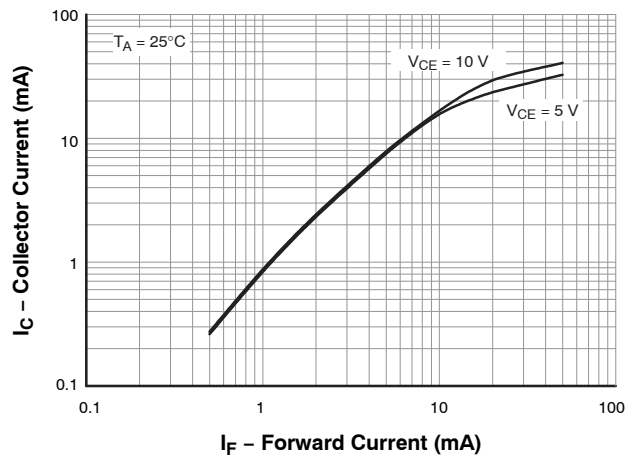


Figure 4. Collector Current vs. Forward Current (FODM121/2701/2705)

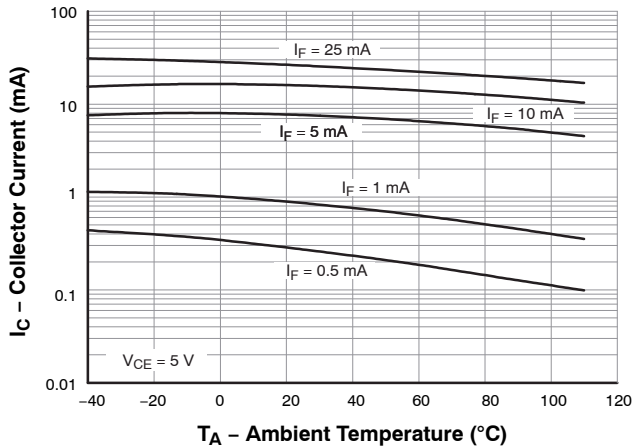


Figure 5. Collector Current vs. Ambient Temperature (FODM121/2701/2705)

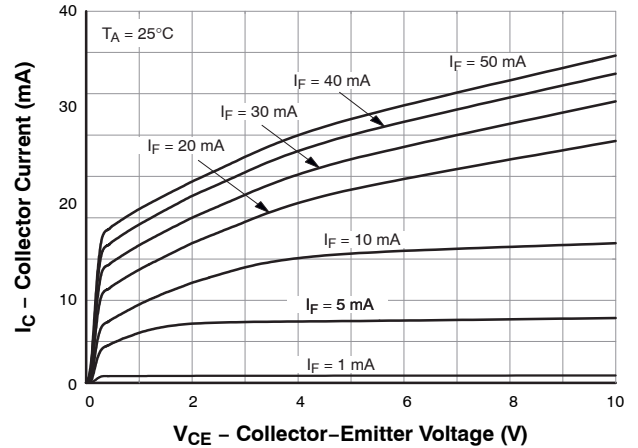


Figure 6. Collector Current vs. Ambient Temperature (FODM121/2701/2705)

TYPICAL PERFORMANCE CURVES (Continued)

($T_A = 25^\circ\text{C}$ unless otherwise specified)

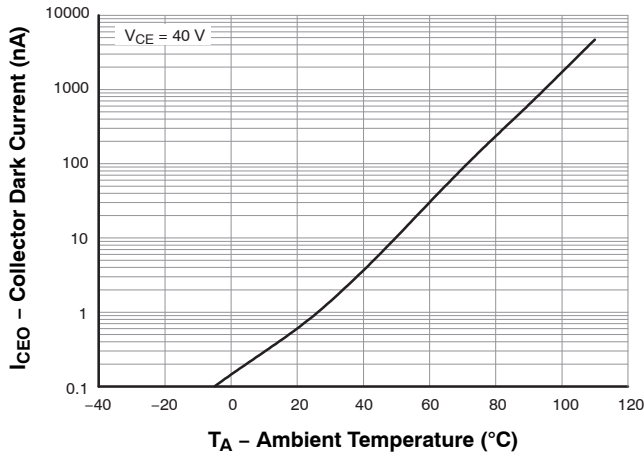


Figure 7. Collector Dark Current vs. Ambient Temperature (FODM121/2701/2705)

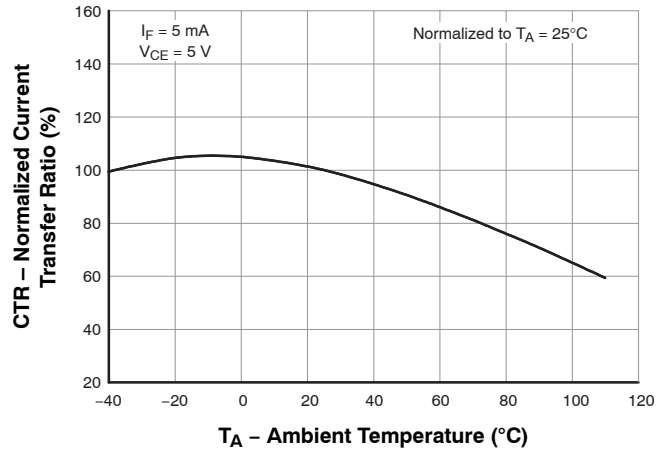


Figure 8. Normalized Current Transfer Ratio vs. Ambient Temperature (FODM121/2701/2705)

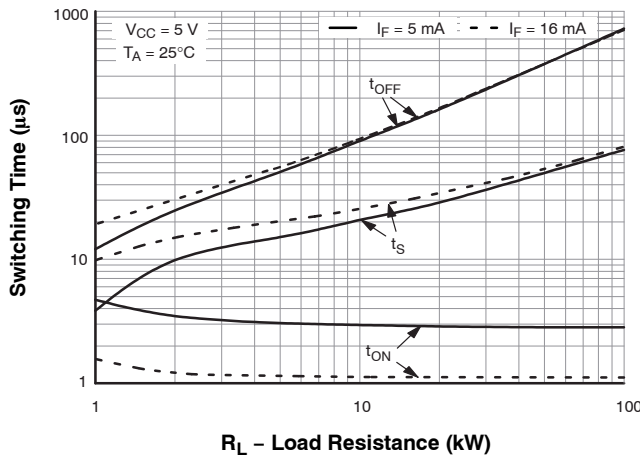


Figure 9. Switching Time vs. Load Resistance (FODM121/2701/2705)

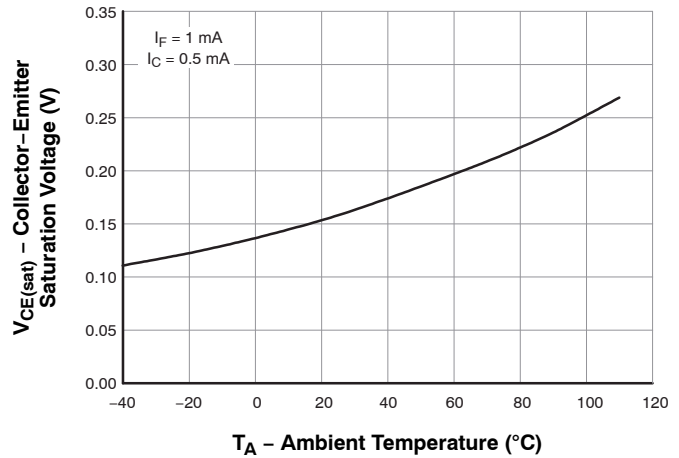


Figure 10. Collector-Emitter Saturation Voltage vs. Ambient Temperature (FODM124)

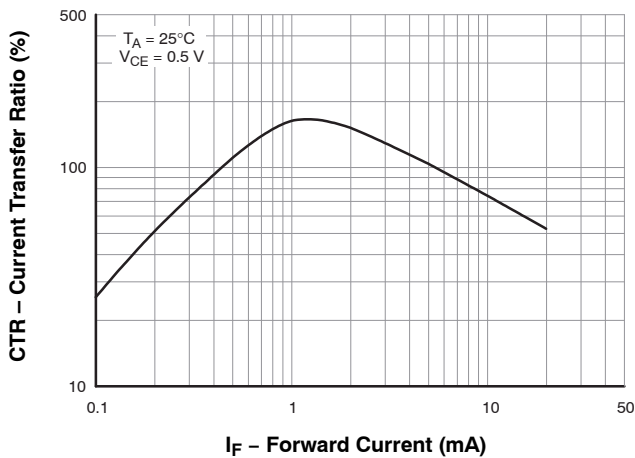


Figure 11. Current Transfer Ratio vs. Forward Current (FODM124)

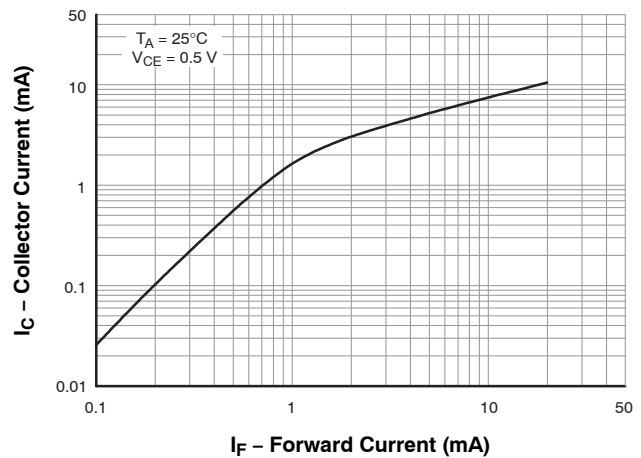


Figure 12. Collector Current vs. Forward Current (FODM124)

TYPICAL PERFORMANCE CURVES (Continued)

($T_A = 25^\circ\text{C}$ unless otherwise specified)

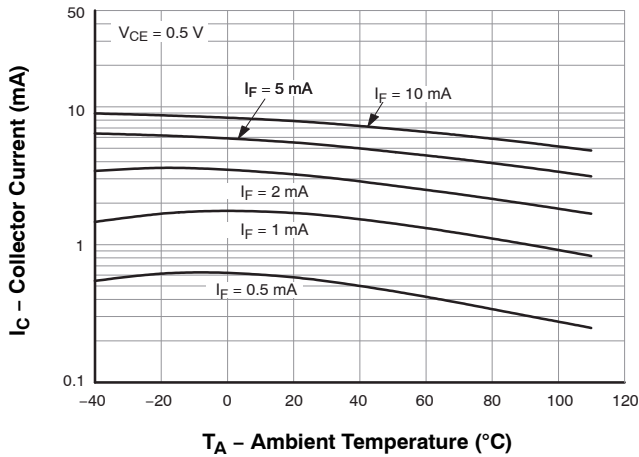


Figure 13. Collector Current vs. Ambient Temperature (FODM124)

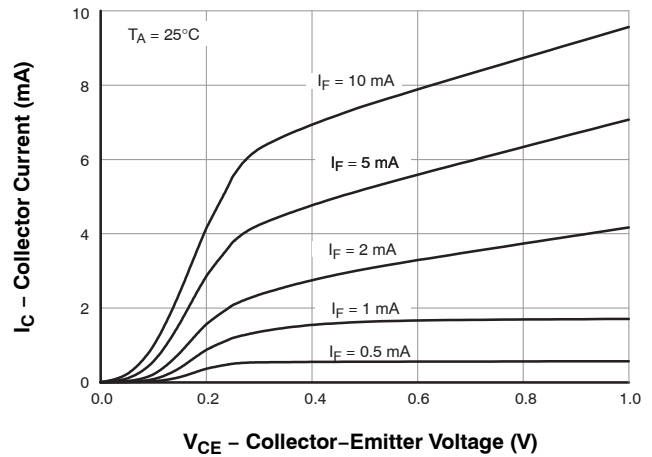


Figure 14. Collector Current vs. Collector-Emitter Voltage (FODM124)

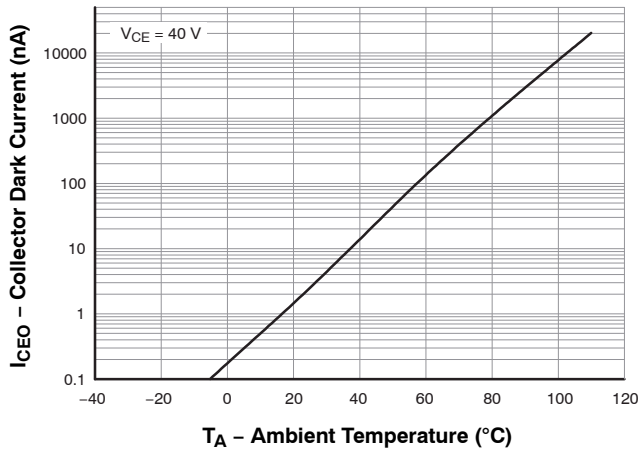


Figure 15. Collector Dark Current vs. Ambient Temperature (FODM124)

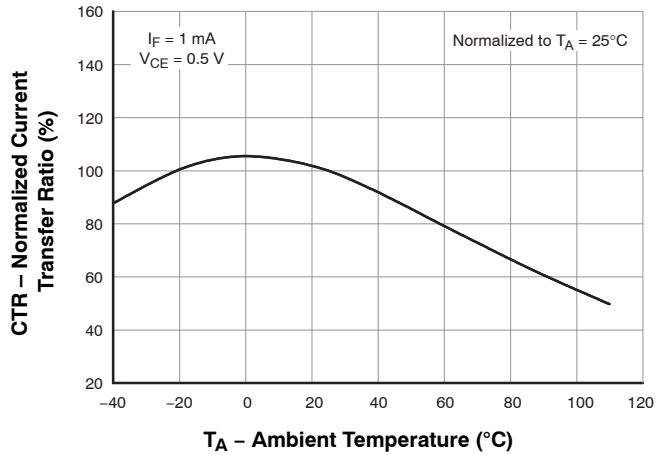


Figure 16. Normalized Current Transfer Ratio vs. Ambient Temperature (FODM124)

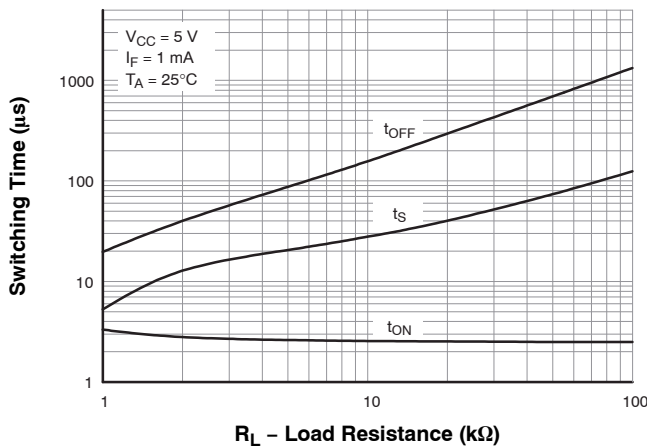
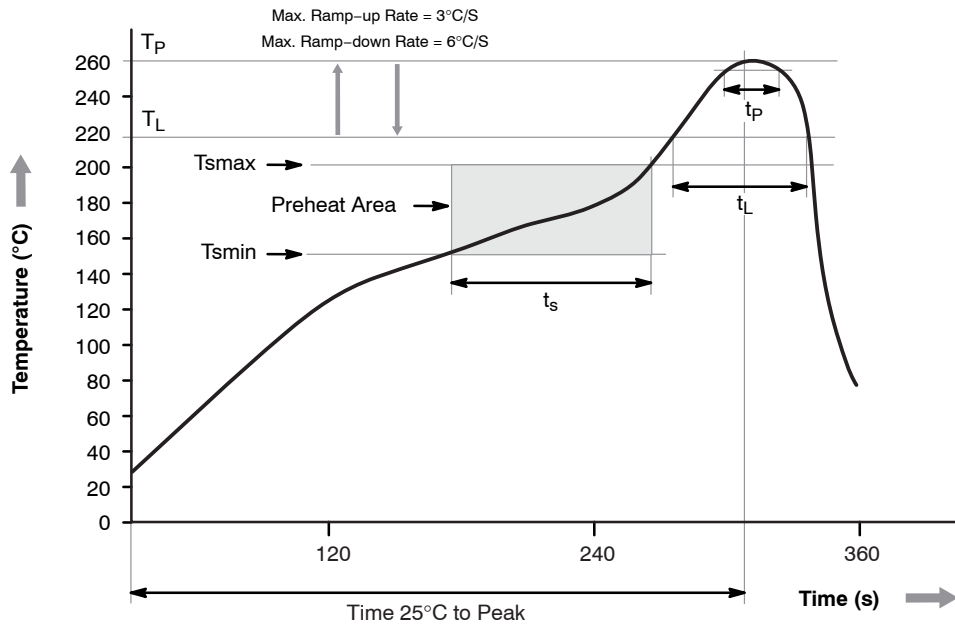


Figure 17. Switching Time vs. Load Resistance (FODM124)

REFLOW PROFILE



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmín)	150°C
Temperature Max. (Tsmáx)	200°C
Time (ts) from (Tsmín to Tsmáx)	60–120 s
Ramp-up Rate (tl to tp)	3°C/second max.
Liquidus Temperature (Tl)	217°C
Time (tl) Maintained Above (Tl)	60–150 s
Peak Body Package Temperature	260°C +0°C / -5°C
Time (tp) within 5°C of 260°C	30 s
Ramp-down Rate (Tp to Tl)	6°C/s max.
Time 25°C to Peak Temperature	8 min max.

ORDERING INFORMATION

Part Number (Note 3)	Package	Shipping†
FODM121	Full Pitch Mini-Flat 4-Pin	100 / Tube
FODM121R2	Full Pitch Mini-Flat 4-Pin	2,500 / Tape and Reel
FODM121V	Full Pitch Mini-Flat 4-Pin, DIN EN/IEC60747-5-5 Option	100 / Tube
FODM121R2V	Full Pitch Mini-Flat 4-Pin, DIN EN/IEC60747-5-5 Option	2,500 / Tape and Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

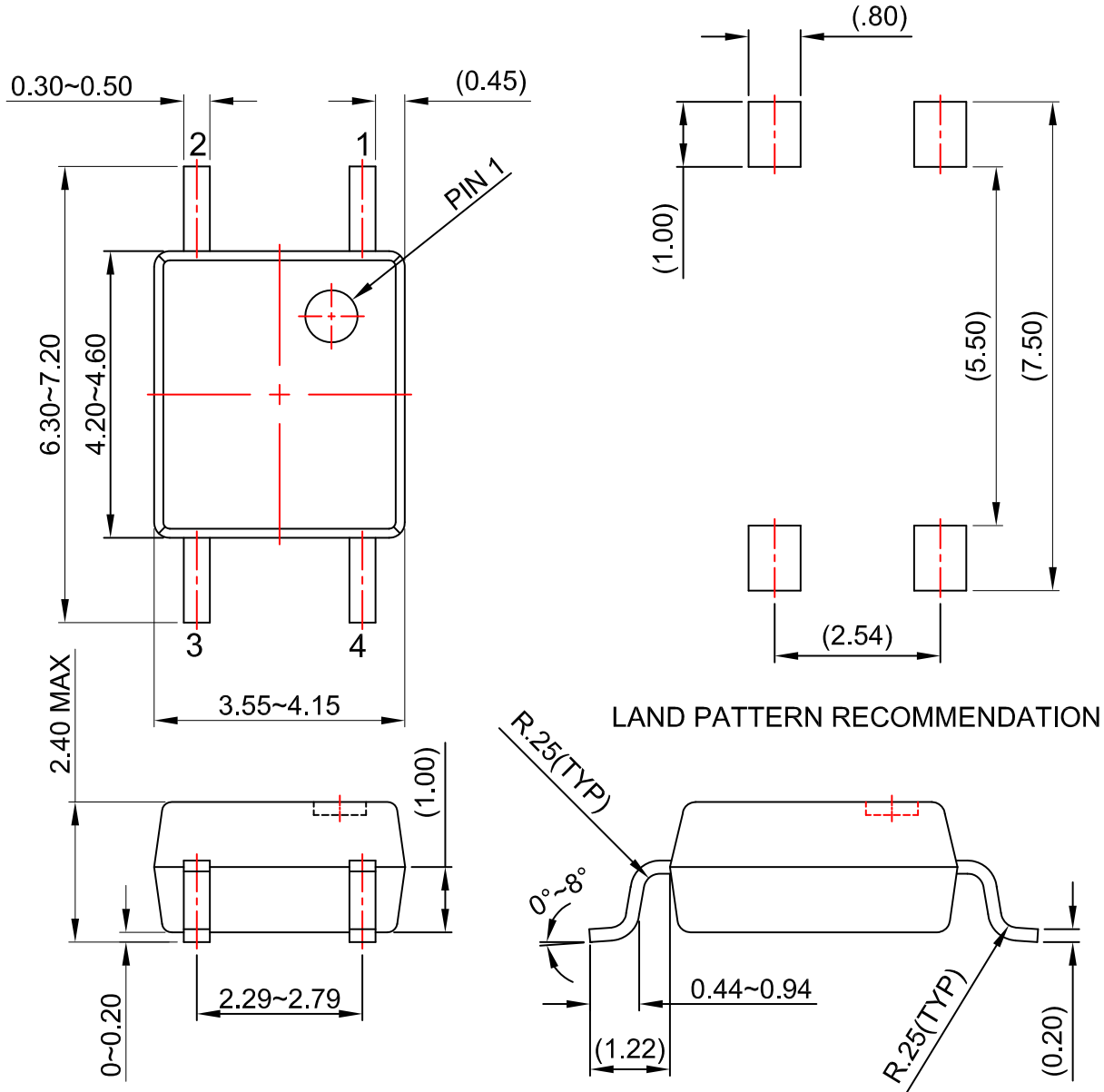
3. The product orderable part number system listed in this table also applies to the FODM121A, FODM121B, FODM121C, FODM124, FODM2701, and FODM2705 products.

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



MFP4 3.85X4.4, 2.54P
CASE 100AP
ISSUE O

DATE 31 AUG 2016



NOTES:

- A) NO STANDARD APPLIES TO THIS PACKAGE.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSION

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